Amendments to the Claims

1. (*Currently Amended*) Method of manufacturing a semiconductor device ~~(10)~~ with a field effect transistor,

_____in which method a semiconductor body ~~(1)~~ of a semiconductor material is provided, at a surface thereof, with a source region ~~(2)~~ and a drain region ~~(3)~~ and with a gate region ~~(4)~~ between the source region ~~(2)~~ and the drain region ~~(3)~~, which gate region comprises

_____a semiconductor region ~~(4A)~~ of a further semiconductor material that is separated from the surface of the semiconductor body ~~(1)~~ by a gate dielectric ~~(5)~~, and

_____with spacers ~~(6)~~ adjacent to the gate region ~~(4)~~ for forming the source and drain regions ~~(2,3)~~,

_____in which method the source region ~~(2)~~ and the drain region ~~(3)~~ are provided with a metal layer ~~(7)~~ which is used to form a compound ~~(8)~~ of the metal and the semiconductor material, and

_____the gate region ~~(4)~~ is provided with a metal layer ~~(7)~~ which is used to form a compound ~~(8)~~ of the metal and the further semiconductor material, characterized in that before the spacers ~~(6)~~ are formed,

_____a sacrificial region ~~(4B)~~ of a material that may be selectively etched with respect to the semiconductor region ~~(4A)~~ is deposited on top of the semiconductor region ~~(4A)~~, and

_____after the spacers ~~(6)~~ have been formed, the sacrificial layer ~~(4B)~~ is removed by etching, and

_____after removal of the sacrificial layer ~~(4B)~~, a single metal layer ~~(7)~~ is deposited contacting the source, drain and gate regions ~~(2,3,4)~~.

2. (*Currently Amended*) A method as claimed in claim 1, characterized in that

the spacers ~~(6)~~ are formed by depositing a layer of a dielectric material on top of the semiconductor body ~~(1)~~ on which the gate region ~~(4)~~ comprising the semiconductor region ~~(4A)~~ and the sacrificial region ~~(4B)~~ is present and by subsequently removing the deposited layer on top of and on both sides of the gate region ~~(4)~~ by etching.

3. (*Currently Amended*) A method ~~as claimed in claim 1 or 2,~~ as claimed in claim 1, characterized in that the semiconductor region ~~(4A)~~ is completely consumed during the formation of the compound ~~(8)~~ of the metal and the further semiconductor material.

4. (*Currently Amended*) A method ~~as claimed in claim 1, 2 or 3,~~ as claimed in claim 1, characterized in that

the formation of the compounds ~~(8)~~ between the metal and the semiconductor material and the metal and the further semiconductor material is carried out in two separate heating steps,

_____the first heating step resulting in an intermediate compound with a low content of the semiconductor material or of the further semiconductor material and in

_____the second heating step the intermediate compound being converted to the compound having a higher content of the semiconductor material or of the further semiconductor material.

5. (*Currently Amended*) A method as claimed in claim 4, characterized in that

_____between the two heating steps, a part of the metal layer ~~(7)~~ which has not reacted to form the intermediate compound is removed by etching.

6. (*Currently Amended*) A method ~~as claimed in claim 4 or 5,~~ as claimed in claim 4, characterized in that between the two heating steps, a layer ~~(44)~~ of the further semiconductor material is deposited on the surface of the semiconductor body ~~(1)~~.

7. (*Currently Amended*) A method as claimed in claim 6, characterized in that after the second heating step, a part of the layer ~~(44)~~ of the further semiconductor material which has not reacted to form the compound is removed by etching.

8. (*Currently Amended*) A method ~~as claimed in anyone of the preceding claims,~~ as claimed in claim 1, characterized in that after the formation of the compounds of the metal and the semiconductor material and of the metal and the further semiconductor material, the spacers (6) are removed.

9. (*Currently Amended*) A method ~~as claimed in anyone of the preceding claims,~~ as claimed in claim 1, characterized in that for the semiconductor material as well as for the further semiconductor material silicon is chosen, and for the intermediate compound and for the compound of the metal and the semiconductor material and the further semiconductor material a metal silicide is chosen.

10. (*Currently Amended*) A semiconductor device ~~(10)~~ comprising a field effect transistor obtained by a method as claimed in anyone of the preceding claims.